TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# **SSM6N7002FU**

High Speed Switching Applications Analog Switch Applications

• Small package

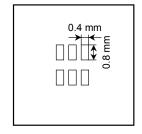
• Low ON resistance :  $R_{on} = 3.3 \Omega \text{ (max) } (@V_{GS} = 4.5 \text{ V})$ 

:  $R_{OR} = 3.2 \Omega$  (max) (@V<sub>GS</sub> = 5 V) :  $R_{OR} = 3.0 \Omega$  (max) (@V<sub>GS</sub> = 10 V)

### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DS}$	60	V	
Gate-Source voltage		V <sub>GSS</sub>	± 20	V	
Drain current	DC	I <sub>D</sub>	200	mA	
	Pulse	I <sub>DP</sub>	800		
Drain power dissipation (Ta = 25°C)		P <sub>D</sub> (Note)	300	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−55~150</b>	°C	

Note: Total rating, mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 t, Cu Pad: 0.32mm $^2$   $\times$  6)

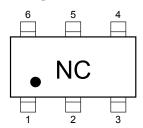


# 1.SOURCE1 4.SOURCE2 2.GATE1 5.GATE2 US6 3.DRAIN2 6.DRAIN1 JEDEC — JEITA —

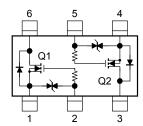
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### Marking



### **Equivalent Circuit (top view)**



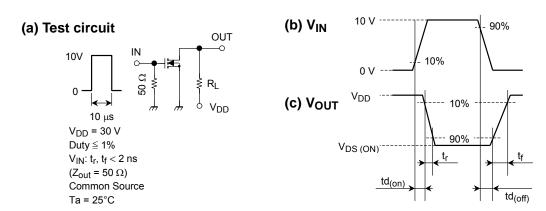
### **Handling Precaution**

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

## Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур	Max	Unit	
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$	_	_	± 10	μА	
Drain-Source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 0.1 mA, V <sub>GS</sub> = 0	60	_	_	V	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0	_	_	1	μΑ	
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.25 mA	1.0	_	2.5	V	
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA	170	_	_	mS	
Drain-Source ON resistance		R <sub>DS (ON)</sub>	I <sub>D</sub> = 500 mA, V <sub>GS</sub> = 10 V	_	2.0	3.0	Ω	
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 5 V	_	2.1	3.2		
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 4.5 V	_	2.2	3.3		
Input capacitance		C <sub>iss</sub>		_	17	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0, f = 1 MHz	_	1.4	_	pF	
Output capacitance		C <sub>oss</sub>			5.8	_	pF	
Switching time	Turn-on delay time	td <sub>(on)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 200 mA,		2.4	4.0	ns	
	Turn-off delay time	td <sub>(off)</sub>	V <sub>GS</sub> = 0 ~ 10V	_	26	40		

### **Switching Time Test Circuit**

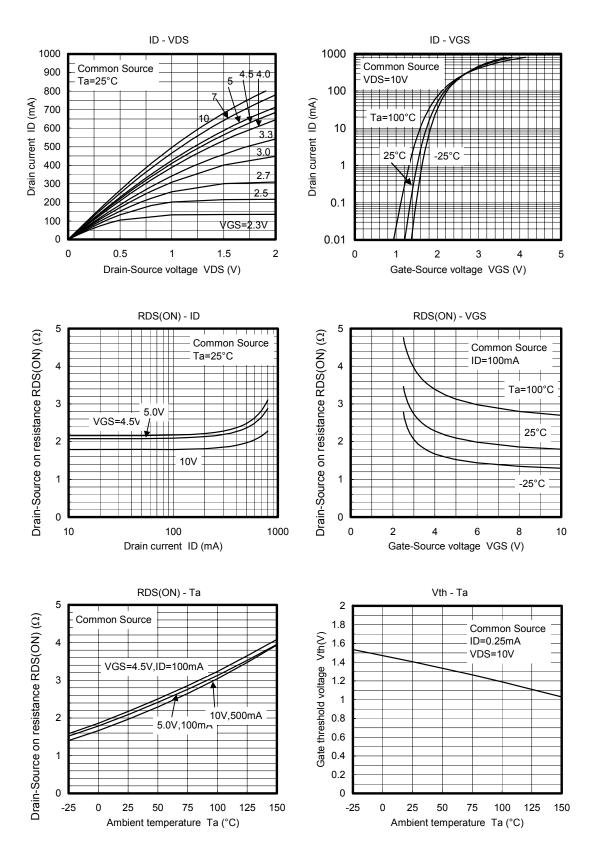


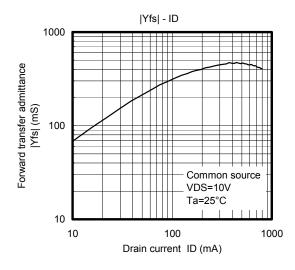
### **Precaution**

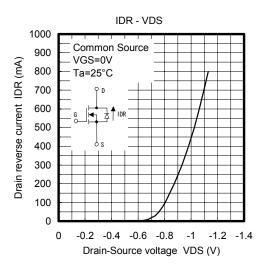
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D$  =250  $\mu$ A for this product. For normal switching operation,  $V_{GS\ (on)}$  requires higher voltage than  $V_{th}$  and  $V_{GS\ (off)}$  requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$ )

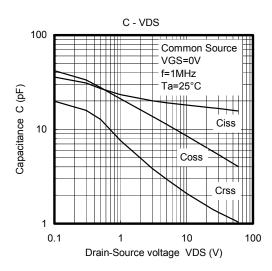
Please take this into consideration for using the device.  $V_{GS}$  recommended voltage of 4.5 V or higher to turn on this product.

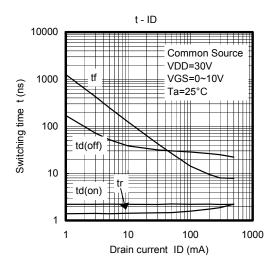
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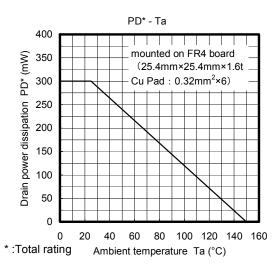












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Handbook" etc..

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